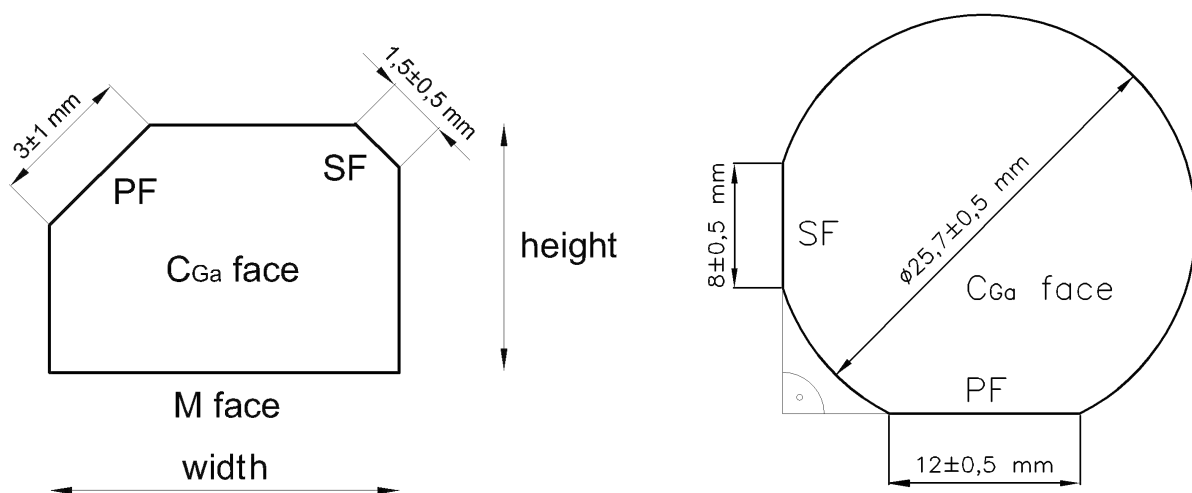


## High-carrier-concentration n-type Ammono-GaN substrates

Features	Units	ORIENTATION		
		c-plane	m-plane	20-21-plane
Carrier concentration	cm <sup>-3</sup>	~ 10 <sup>19</sup>		
Resistivity	Ω·cm	10 <sup>-3</sup> - 10 <sup>-2</sup>		
Mobility	cm <sup>2</sup> /V·s	~ 150		
Thickness	μm	300-400		
Total thickness variation (TTV)	μm	< 40	~ 20	~ 20
Bow	μm	≤ 10		
FWHM of X-ray rocking curve, epi-ready surface at 100 μm x 100 μm slit)	arcsec	~ 20	~ 30	~ 30
Dislocation density	cm <sup>-2</sup>	~ 5·10 <sup>4</sup>		
Misorientation	deg	On demand		
Surface finishing		As cut / ground Roughly polished Optically polished (RMS < 3 nm) Epi-ready (RMS < 0.5 nm)		
Available sizes		10 x 10 mm <sup>2</sup> 1", 2"	9 x 13 mm <sup>2</sup>	10 x 10 mm <sup>2</sup> 13 x 15 mm <sup>2</sup>
Packaging		Separate single wafer container		
Special Order Option		Please, contact Sales Department		



Rectangular and 1" round substrates

*Note: The information given above may be subject to change at any time without notice. This leaflet is not an offer within the meaning of sales or commercial law. The Ammono GaN substrates are offered for sale under Ammono's General Terms and Conditions.*